

IN THE CLAIMS

1.-9. (canceled)

10. (currently amended): A transfer substrate for electrode transfer therefrom onto a semiconductor device, comprising:

a substrate composed of a transparent material;

a seed film on the substrate; and

a patterning film on the substrate, the patterning film partly covering a surface of the seed film so as to expose a metal electrode receiving portion of the seed film;

wherein the seed film is locally present in an area including the metal electrode receiving portion and is absent from other areas of the substrate.

11. (currently amended): [[A]] The transfer substrate according to claim 10, further comprising a metal electrode portion provided on the exposed metal electrode receiving portion of the seed film.

12. (currently amended): [[A]] The transfer substrate according to claim 10, wherein the seed film is composed of such a material that the metal electrode portion has a lower adhesion affinity for the seed film than for a portion of the semiconductor device onto which the metal electrode portion is to be transferred.

13. (new): The transfer substrate according to claim 10, wherein the patterning film is transparent, whereby the semiconductor substrate is visible through the transfer substrate and patterning film, whereby the transfer substrate is positionable relative to the semiconductor substrate.

14. (new): The transfer substrate according to claim 13, wherein the patterning film is an insulating film.

15. (new): The transfer substrate according to claim 14, wherein the insulating film comprises silicon oxide or silicon nitride.

16. (new): The transfer substrate according to claim 1, wherein, within an area of the substrate covered by the patterning film, the seed film is locally present only in areas generally coincident with the metal electrode receiving portions and interconnection film portions interconnecting the metal electrode receiving portions, and is absent from other areas of the substrate covered by the patterning film.